

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	3	carbon near5 SiGe and poly-Si and stack	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/01 11:27
S2	3	carbon near5 SiGe and poly-Si and stack	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/19 11:18
S3	5	Silicon adj germanium near5 carbon and polysilicon same (stack or gate adj stack)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/19 11:23
S4	332	Silicon adj germanium adj carbon same gate and polysilicon same (stack or gate adj stack)or SiGeC	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/19 13:11
S5	13	gate and polysilicon same (stack or gate adj stack)and SiGeC	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/19 13:16
S6	222	polysilicon adj seed adj layer near "5" carbon and lightly adj doped and extension	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:12
S7	0	polysilicon adj seed adj layer near5 carbon and lightly adj doped and extension	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:14
S8	0	polysilicon adj seed adj layer same carbon and lightly adj doped and extension	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:13
S9	2	seed adj layer same carbon and lightly adj doped and extension	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:13
S10	0	polysilicon adj seed adj layer near5 carbon and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:14
S11	0	polysilicon adj seed adj layer same carbon and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:14
S12	0	silicon adj seed adj layer same carbon and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 14:15

S13	27	seed adj layer same carbon and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 15:25
S14	1	silicon near5 seed adj layer same carbon and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 15:35
S15	0	LDD and SiGe and extension and "400" adj Angstroms	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 15:38
S16	6	LDD and SiGe and extension and Angstroms	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 16:18
S17	6	LDD same extension and Angstroms and (polysilicon and silicon adj germanium) same gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 16:29
S18	3	LDD same extension and Angstroms same (polysilicon and silicon adj germanium) same gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 19:27
S19	10	LDD same extension and Angstroms same (lower and upper) same gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 19:30
S20	45	extension and Angstroms same (lower and upper) same gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 19:31
S21	7	LDD and Angstroms same (lower and upper) adj gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 19:35
S22	18	LDD and Angstroms and (lower and upper) adj gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/20 19:35
S23	18574	SiGe or silicon adj germanium	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/28 12:14
S24	10023	(SiGe or silicon adj germanium) and thickness	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/28 12:14

S25	713	((SiGe or silicon adj germanium) and thickness) and (LDD or lightly adj doped adj drain)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/28 12:15
S26	555	((SiGe or silicon adj germanium) and thickness) and (LDD or lightly adj doped adj drain)) and (sidewall or spacer)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/28 12:51
S27	313	(257/297).CCLS.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/10/28 12:52
S28	2949	Sige and thickness	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/11/01 11:29
S29	2974	Sige and thickness	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 11:29
S30	197	Sige and thickness and LDD	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 11:30
S31	195	Sige and thickness and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 12:02
S32	308	(Sige or silicon adj germanium) same thickness and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:05
S33	2	polysilicon same thickness and gatestack and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:09
S34	1	polysilicon same ang and gatestack and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:10
S35	1	silicon same ang and gatestack and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:10
S36	1	silicon same thickness and gatestack and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:10

S37	5354	silicon same thickness and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:10
S38	3301	polysilicon same thickness and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:11
S39	0	polysilicon same "1000 thickness" and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:11
S40	4711	polysilicon same "1000" same "100" same "10" thickness and gate adj oxide and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:16
S41	4324	polysilicon same "1000" same "100" same "10 nm" thickness and gate adj oxide and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:17
S42	4319	polysilicon same "1000" same "100 nm" same "10 nm" thickness and gate adj oxide and LDD and @ad<="20030716"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:17
S43	4319	polysilicon same "1000" same "100 nm" same "10 nm" thickness and gate adj oxide and LDD and @ad<="20030716" and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:37
S44	6	SiGe adj gate and thickness and gate adj oxide and LDD and @ad<="20030716" and gate	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/01 16:38
S45	2	poly-SiGe near5 carbon	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 13:10
S46	1668	(438/270).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/05 18:41
S47	47	S46 and (SiGe or silicon adj germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:05
S48	426	(438/299).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/01 16:29

S49	1026	(438/303).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/01 16:29
S50	113	S49 and (SiGe or silicon adj germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/01 16:37
S51	989	(438/592).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/01 16:37
S52	92	S51 and (SiGe or silicon adj germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/01 16:39
S53	17	S51 and (SiGe or silicon adj germanium)and carbon	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/01 16:40
S54	198	(438/157).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/05 18:41
S55	2678	carbon near5 (SiGe or silicon adj germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:43
S56	754	carbon near5 (SiGe or silicon adj germanium) and gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:44
S57	296	carbon near5 (SiGe or silicon adj germanium) and gate and (poly-Si or polysilicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/05 18:44
S58	0	("2005/0014353").URPN.	USPAT	OR	OFF	2005/08/05 18:52
S59	7	("20020033511" "20020151153" "5185280" "6030874" "6096617" "6153920" "6306712").PN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/08/05 20:12
S60	2	("5998289").PN.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/05 20:12